

FIG. 1A

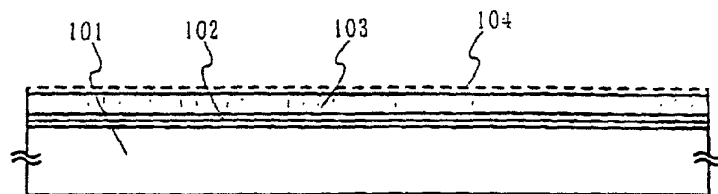


FIG. 1B

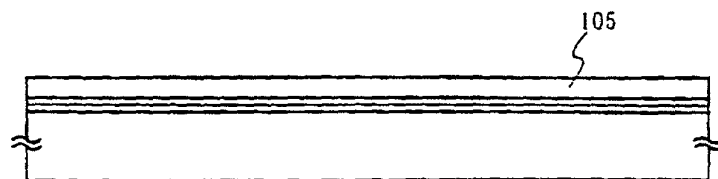


FIG. 1C

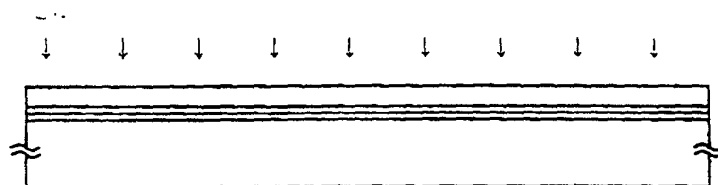


FIG. 1D

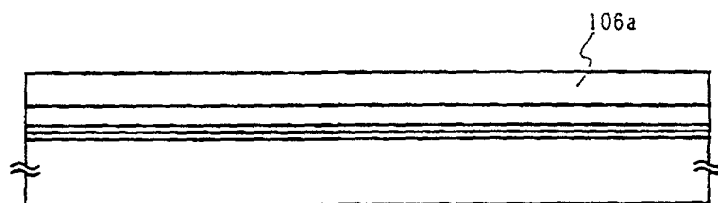


FIG. 2A

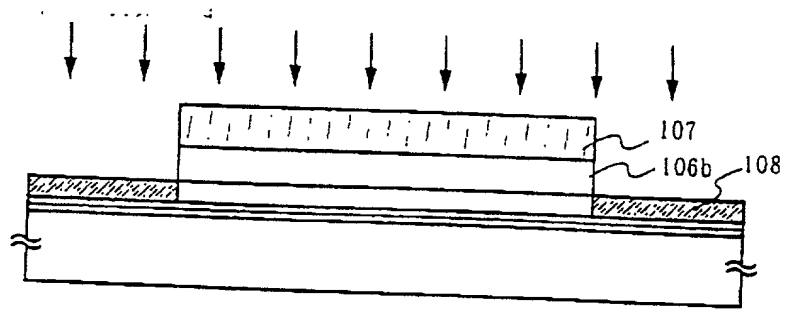


FIG. 2B

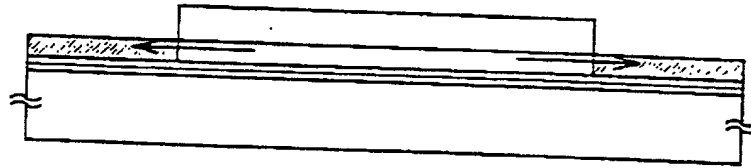


FIG. 2C

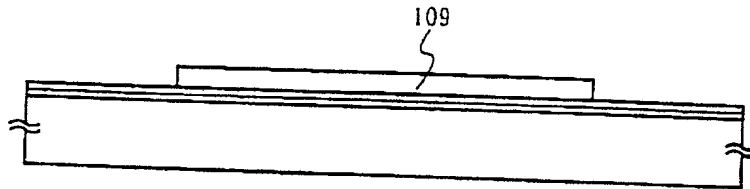


FIG. 2D

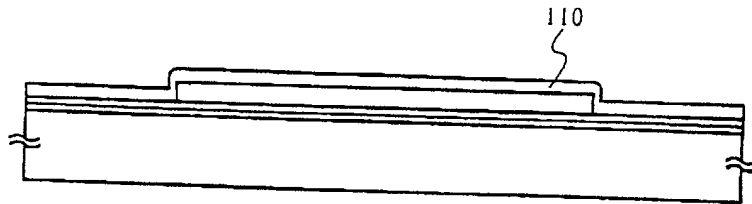


FIG. 3A

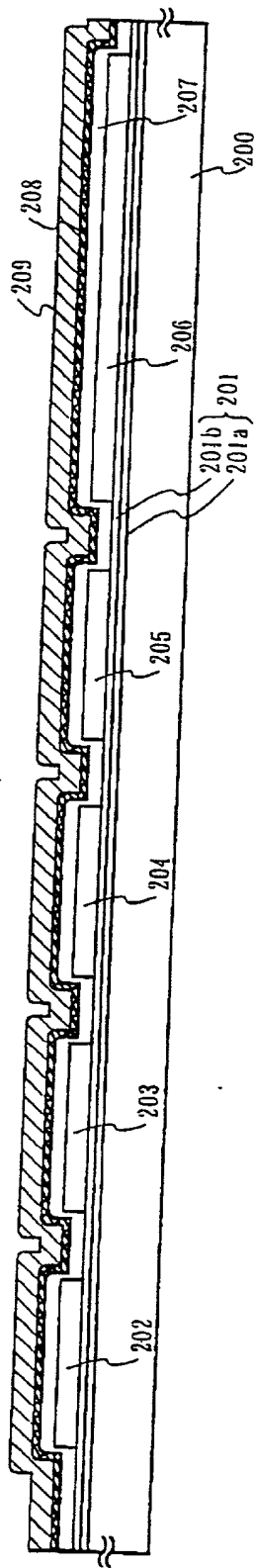


FIG. 3B

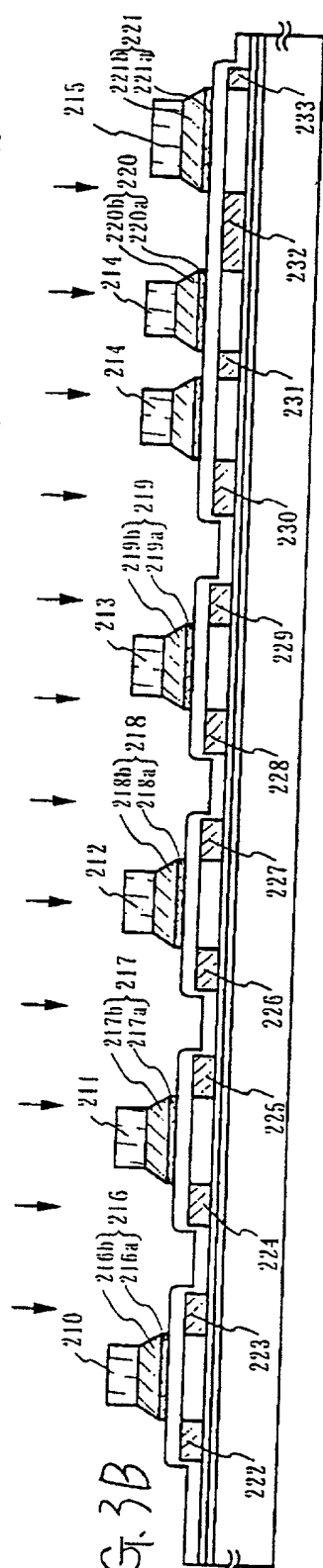


FIG. 3C

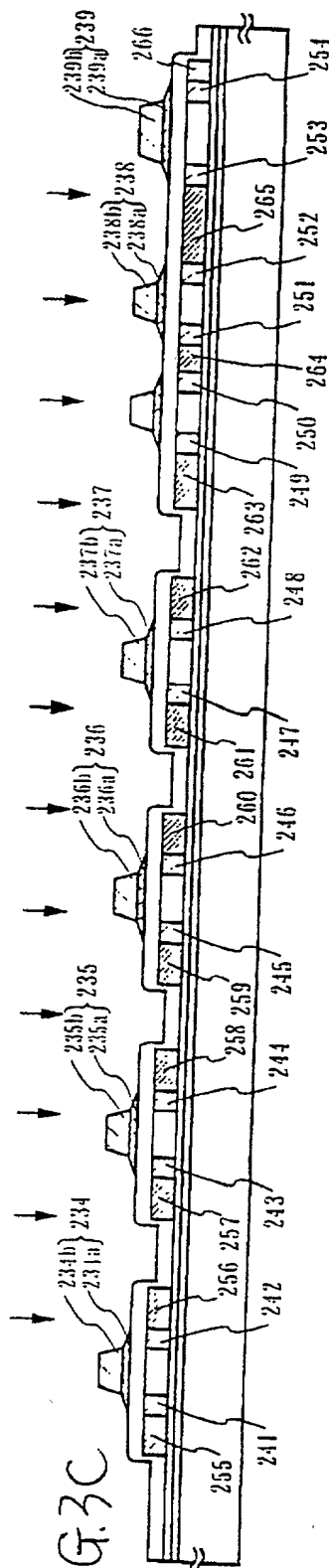


FIG. 4A

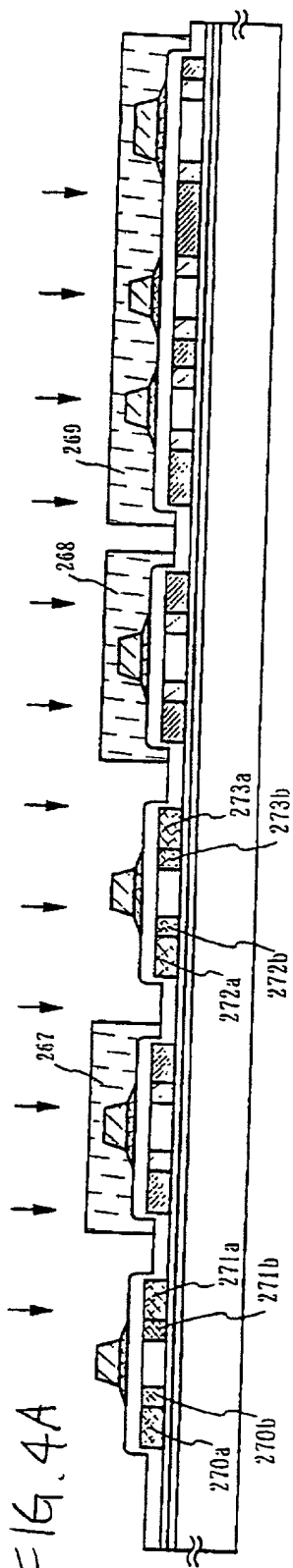


FIG. 4B

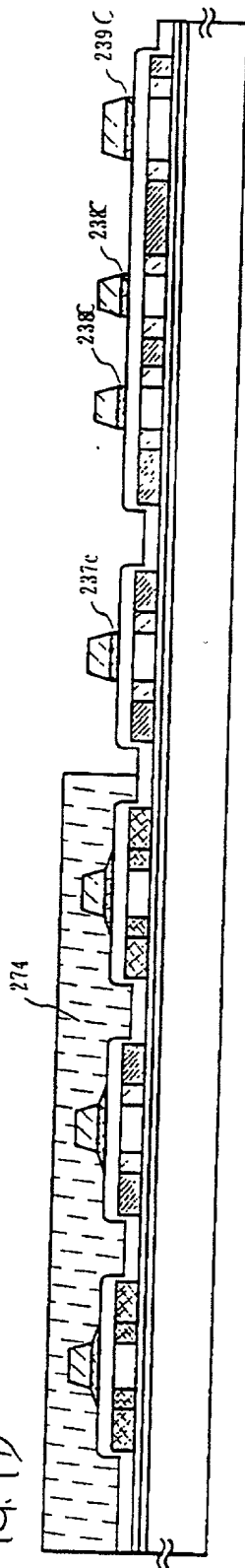
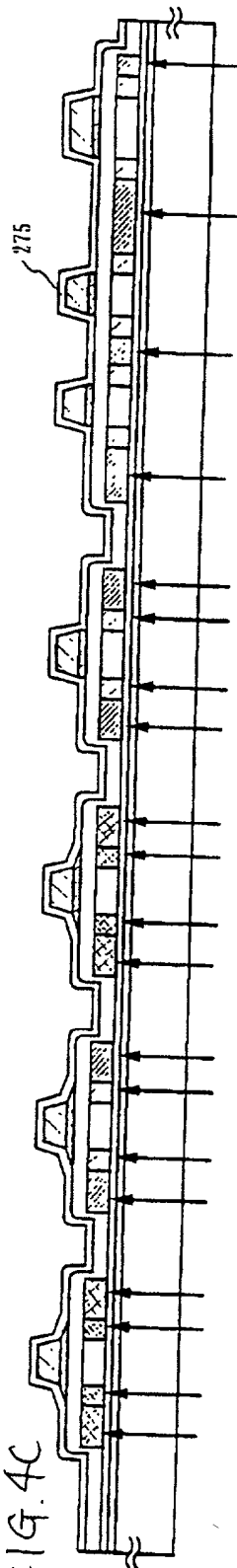


FIG. 4C





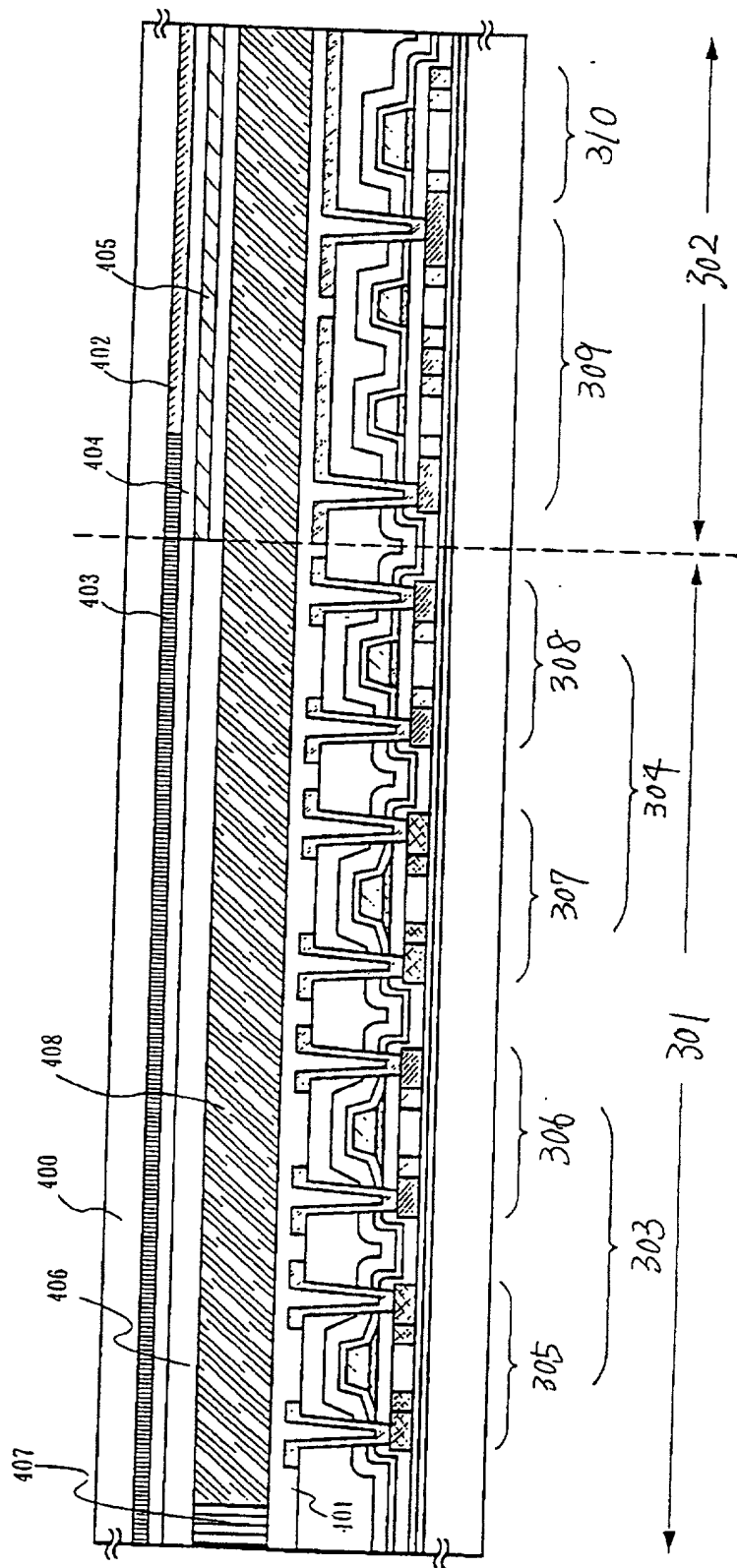


FIG. 6

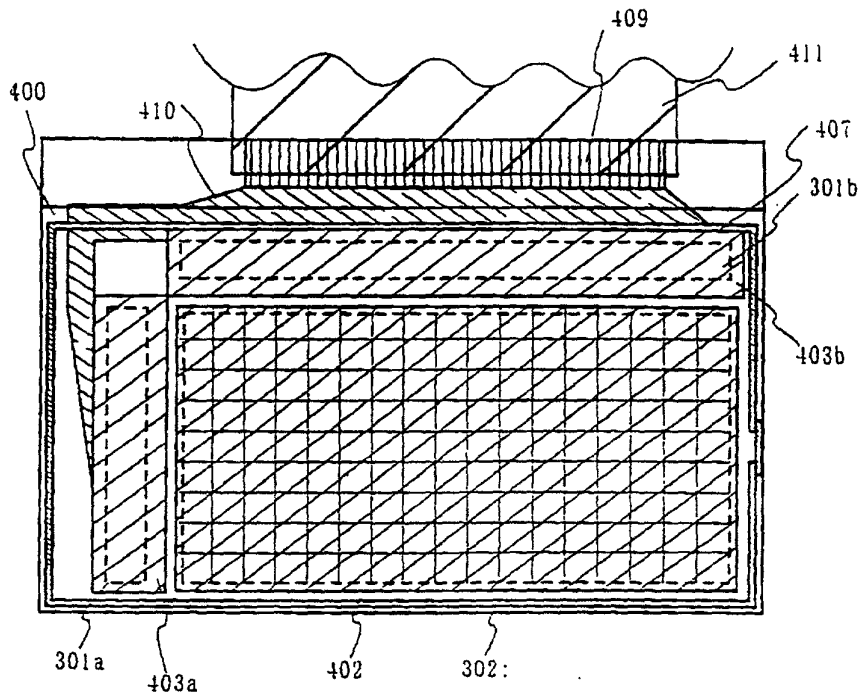


FIG. 7

2025-01-10 10:45:03

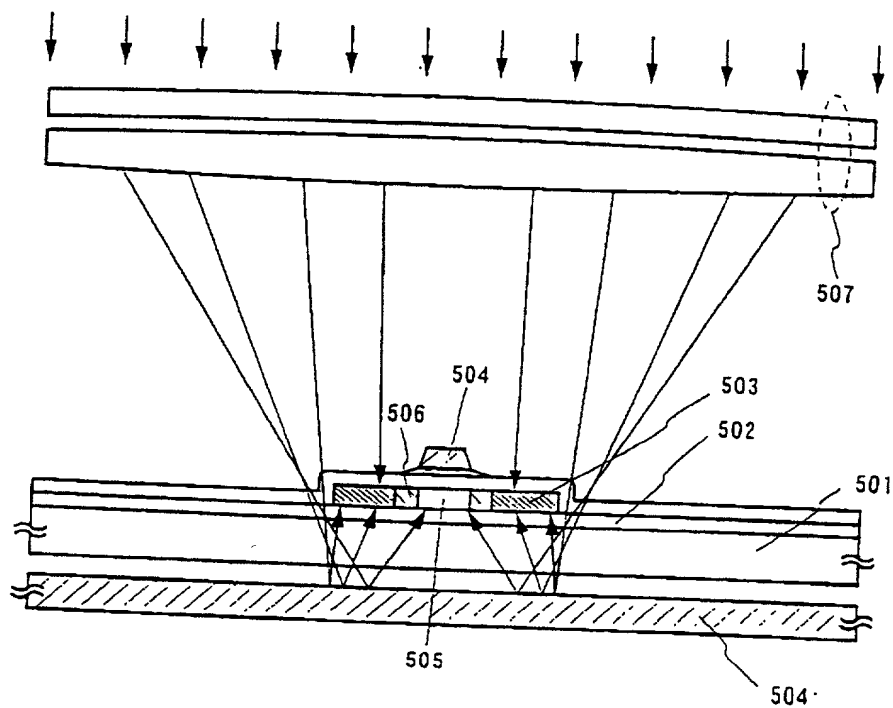


FIG. 8



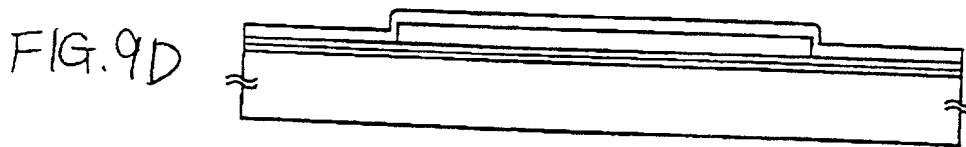
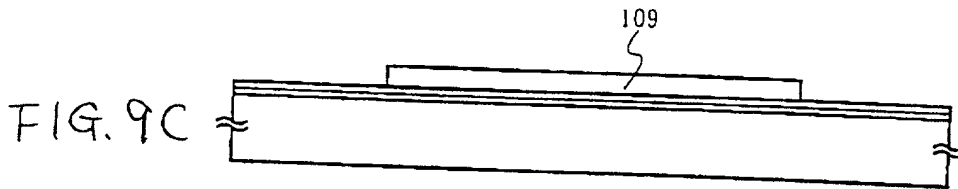
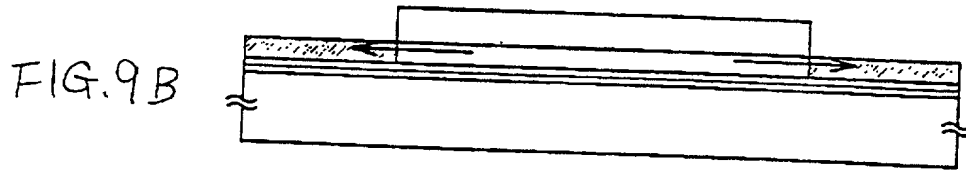
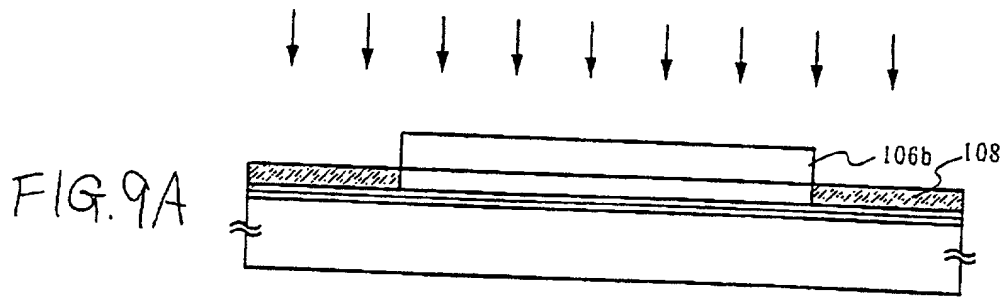


FIG. 10A

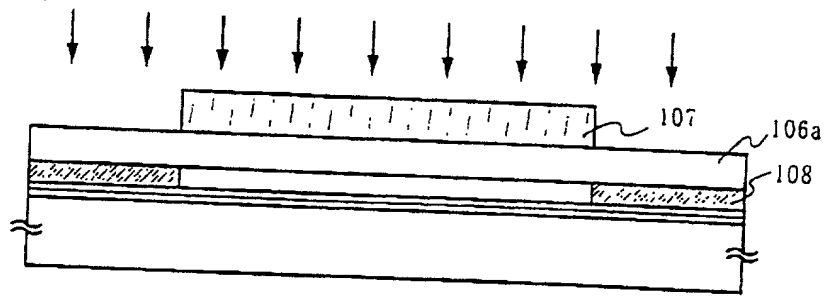


FIG. 10B

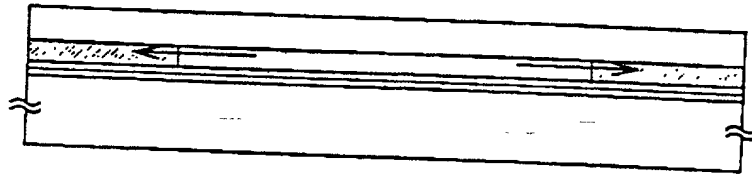


FIG. 10C

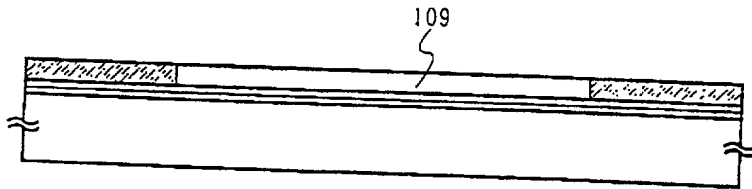


FIG. 10D

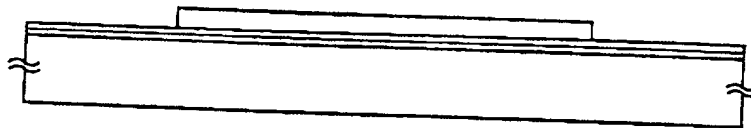


FIG. 11A

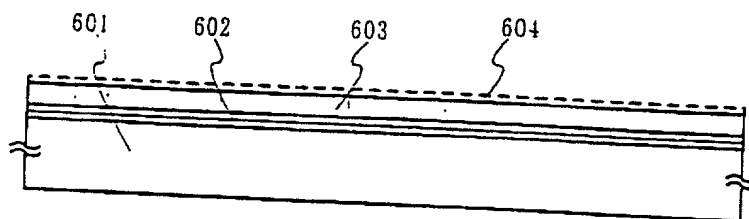


FIG. 11B

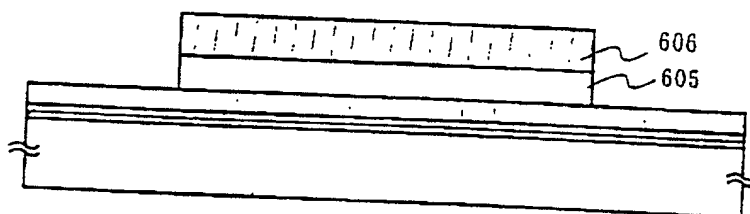


FIG. 11C

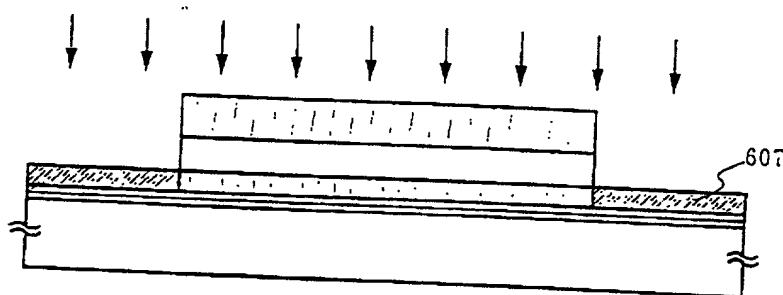


FIG. 11D

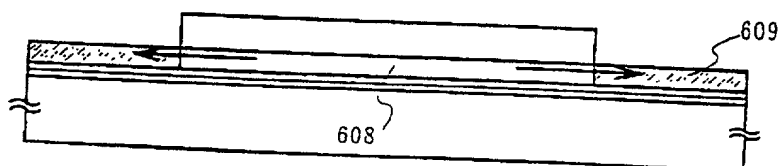
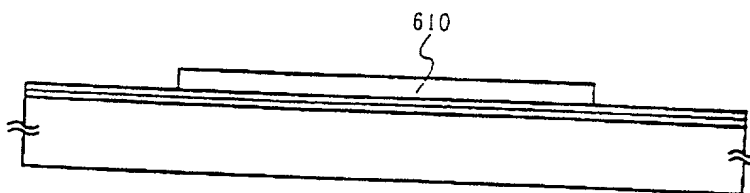


FIG. 11E



2025-03-04 10:46:03

FIG. 12A

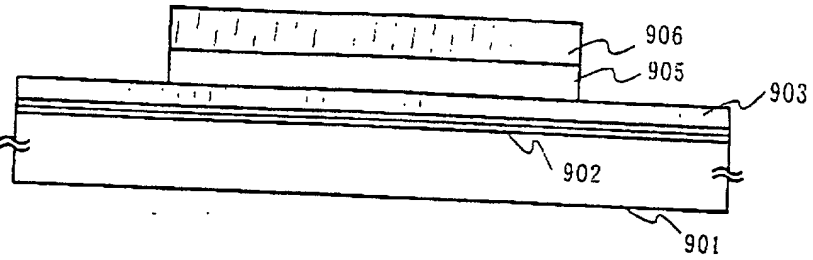


FIG. 12B

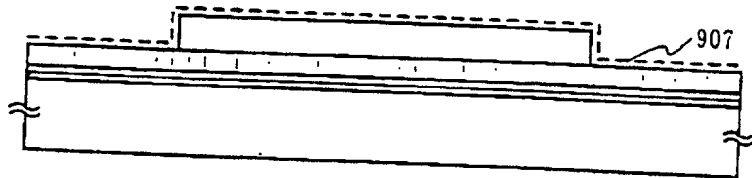


FIG. 12C

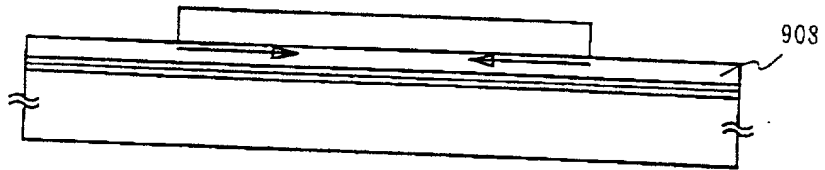


FIG. 12D

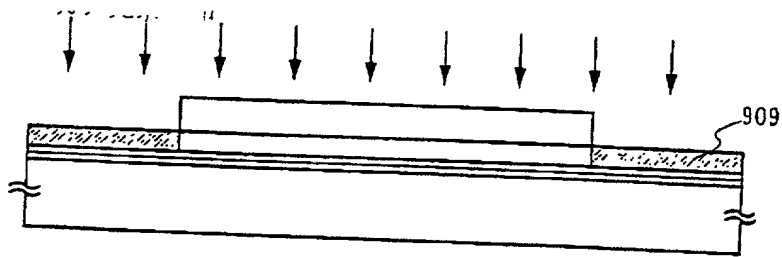


FIG. 12E

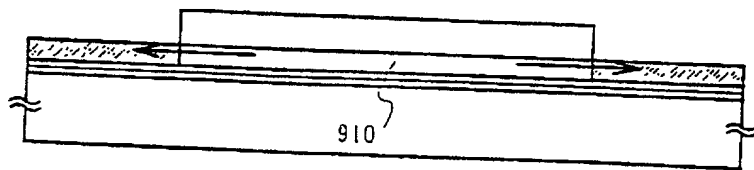


FIG. 12F

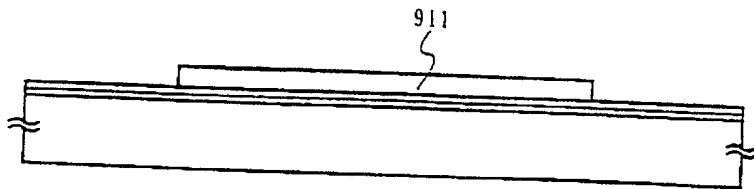


FIG. 13A

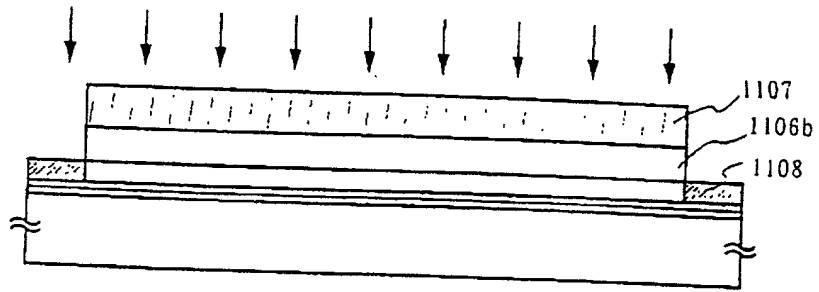


FIG. 13B

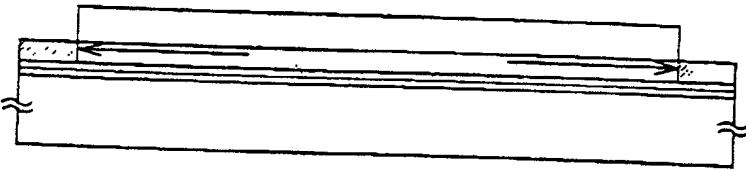


FIG. 13C

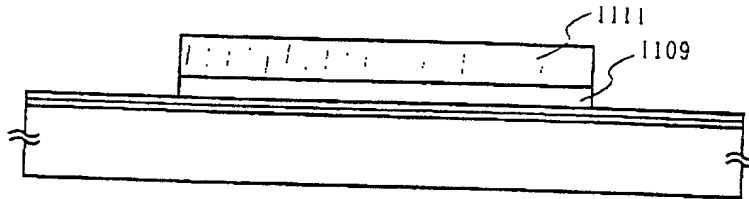


FIG. 13D

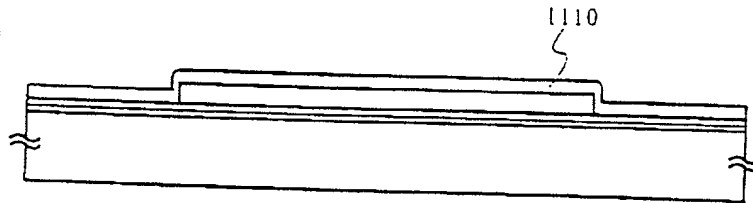


FIG. 14A

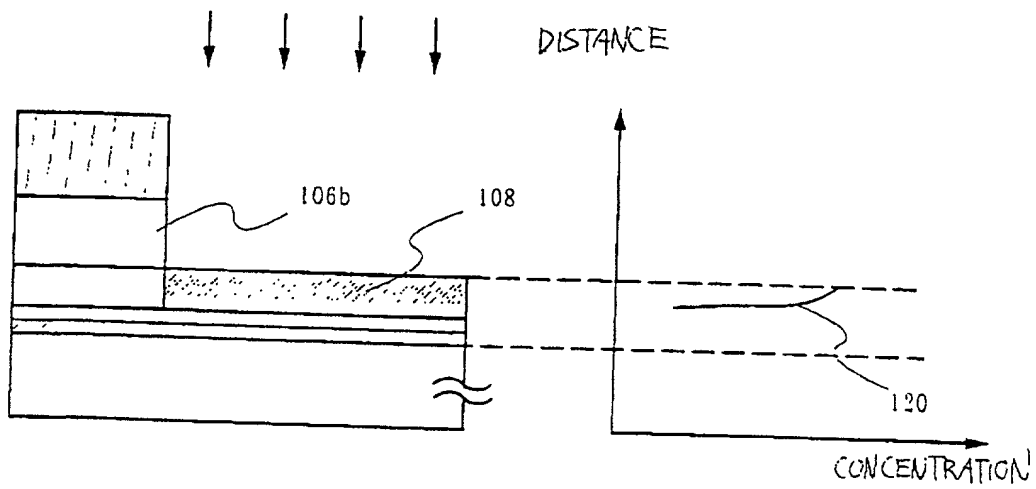


FIG. 14B

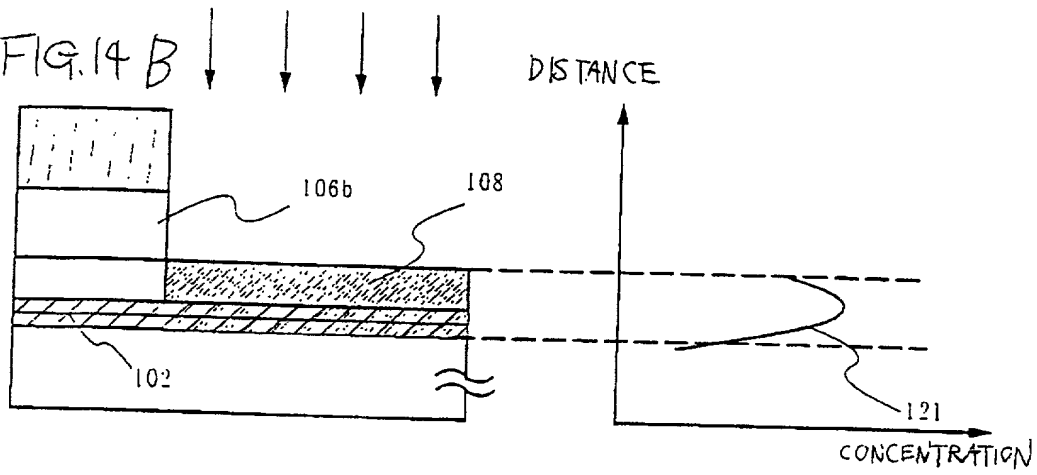
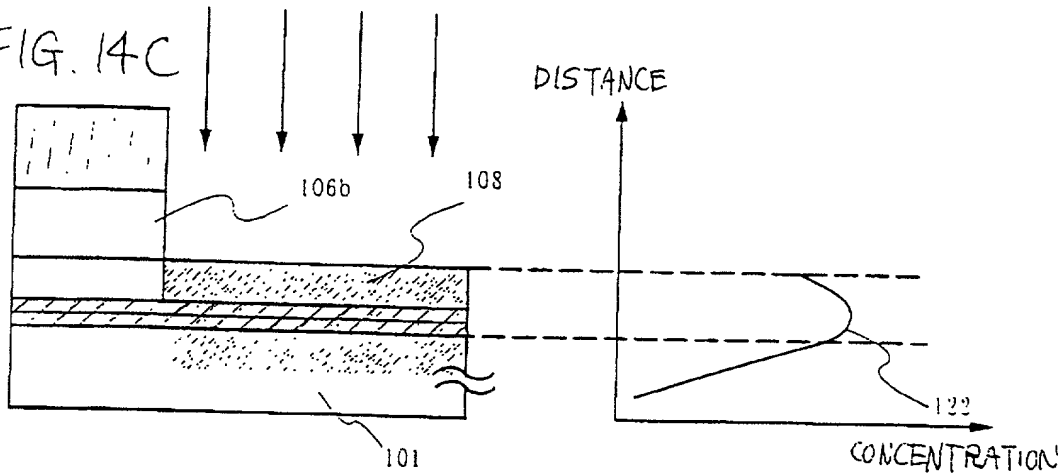


FIG. 14C



2024-06-28 10:00

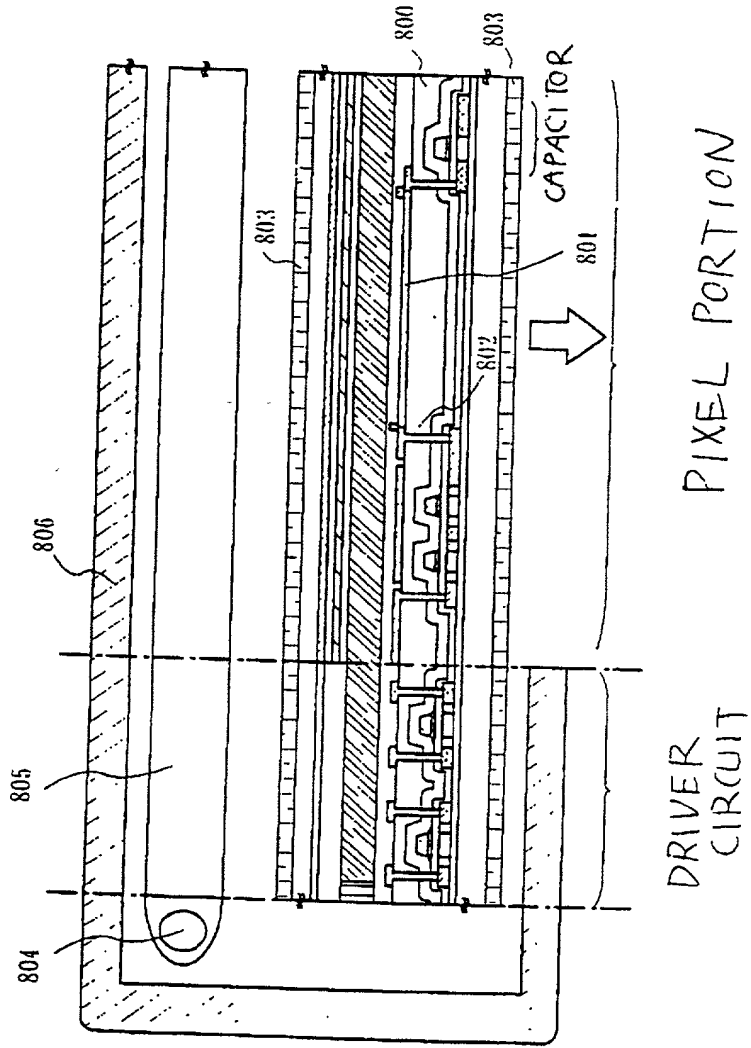
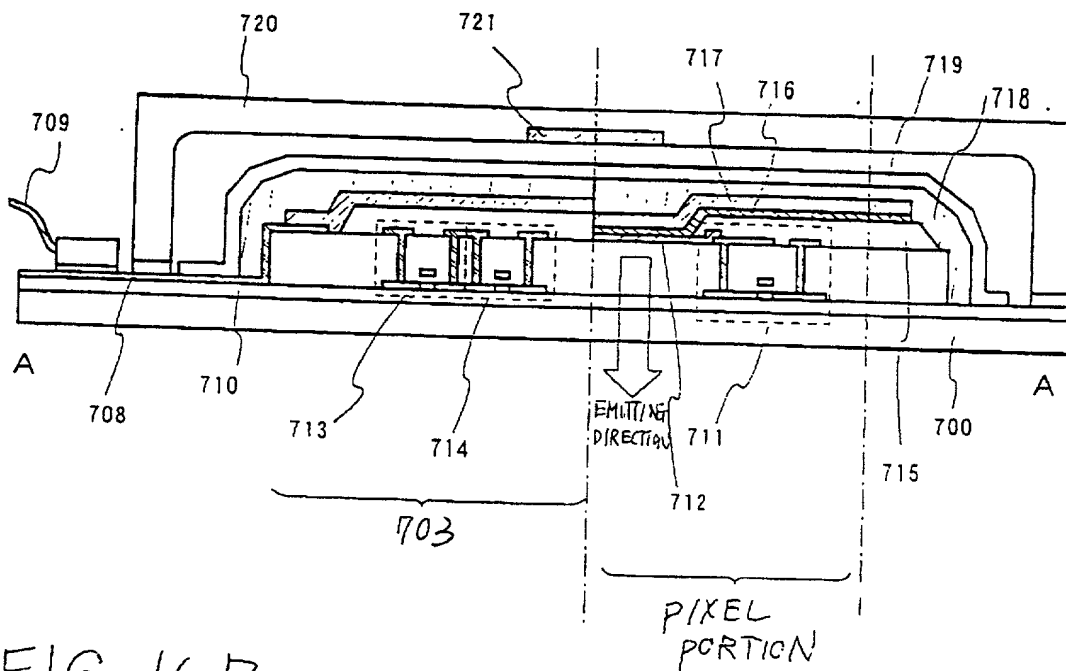
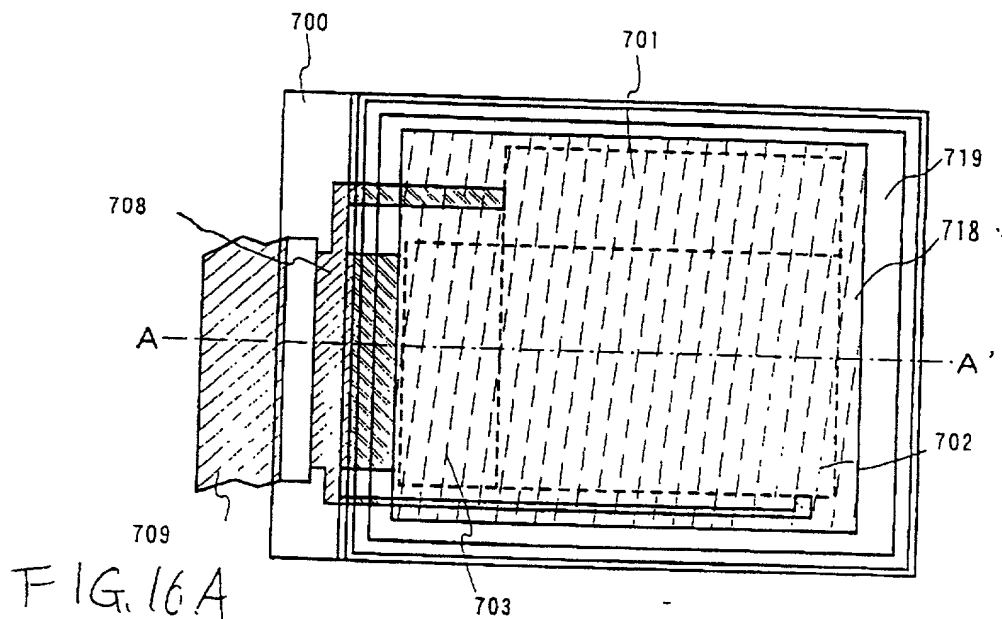


FIG. 15





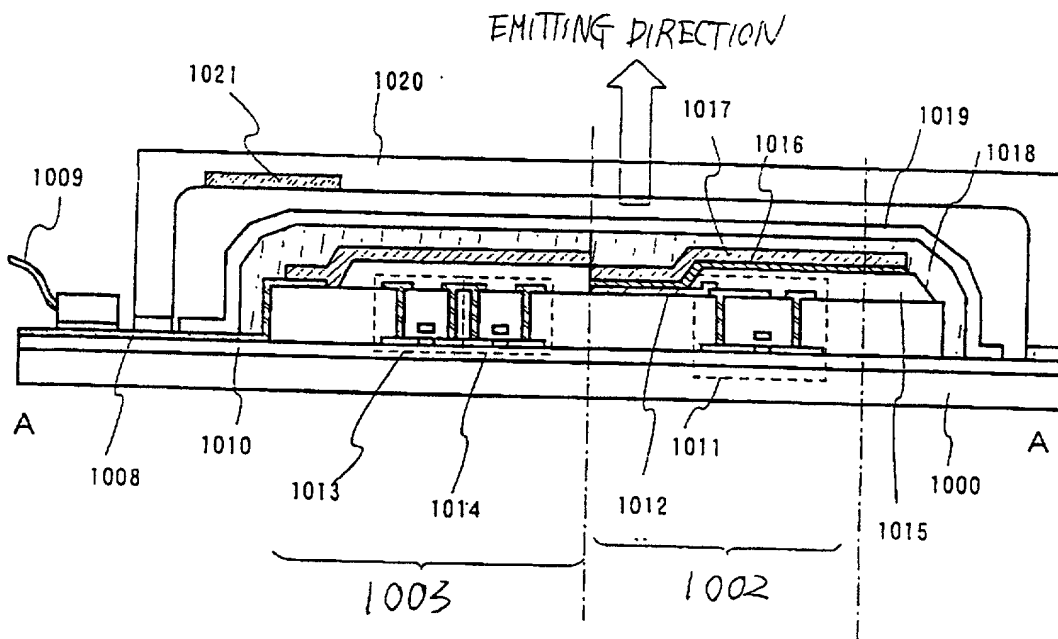


FIG. 17

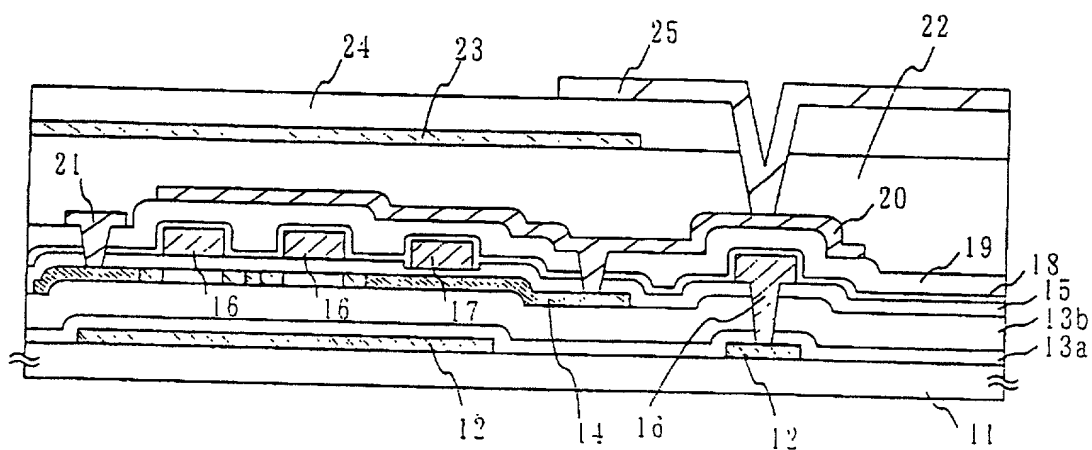


FIG. 18

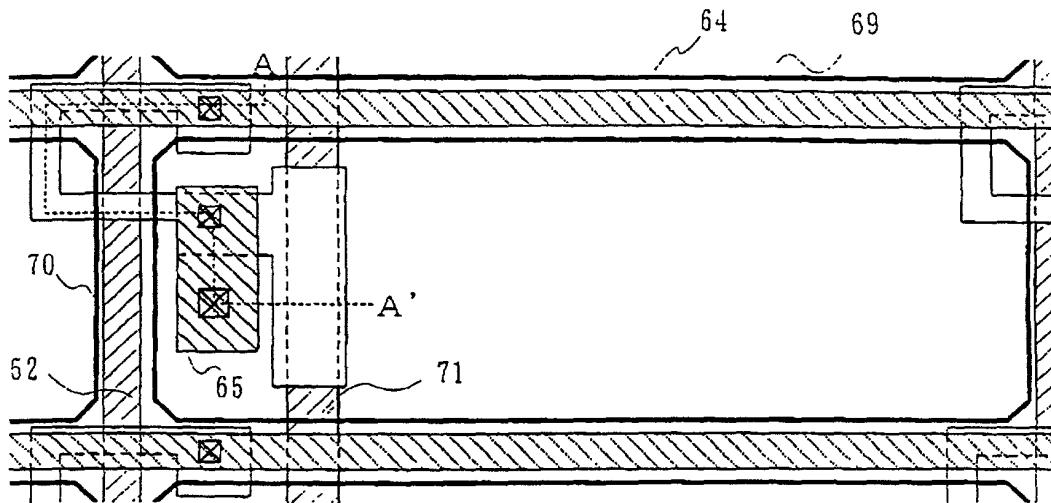


FIG. 19A

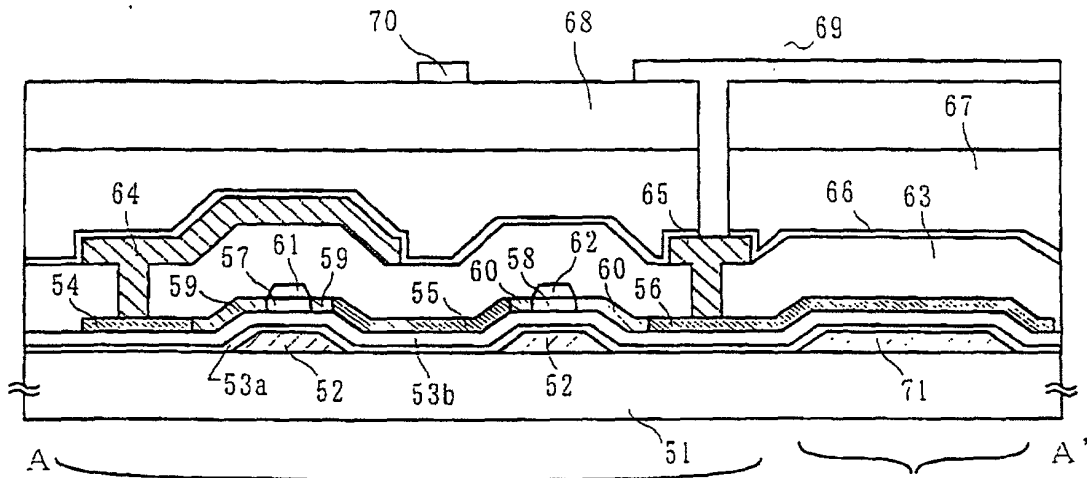


FIG. 19B

PIXEL TFT PORTION

CAPACITOR  
PORTION

20240603-011702

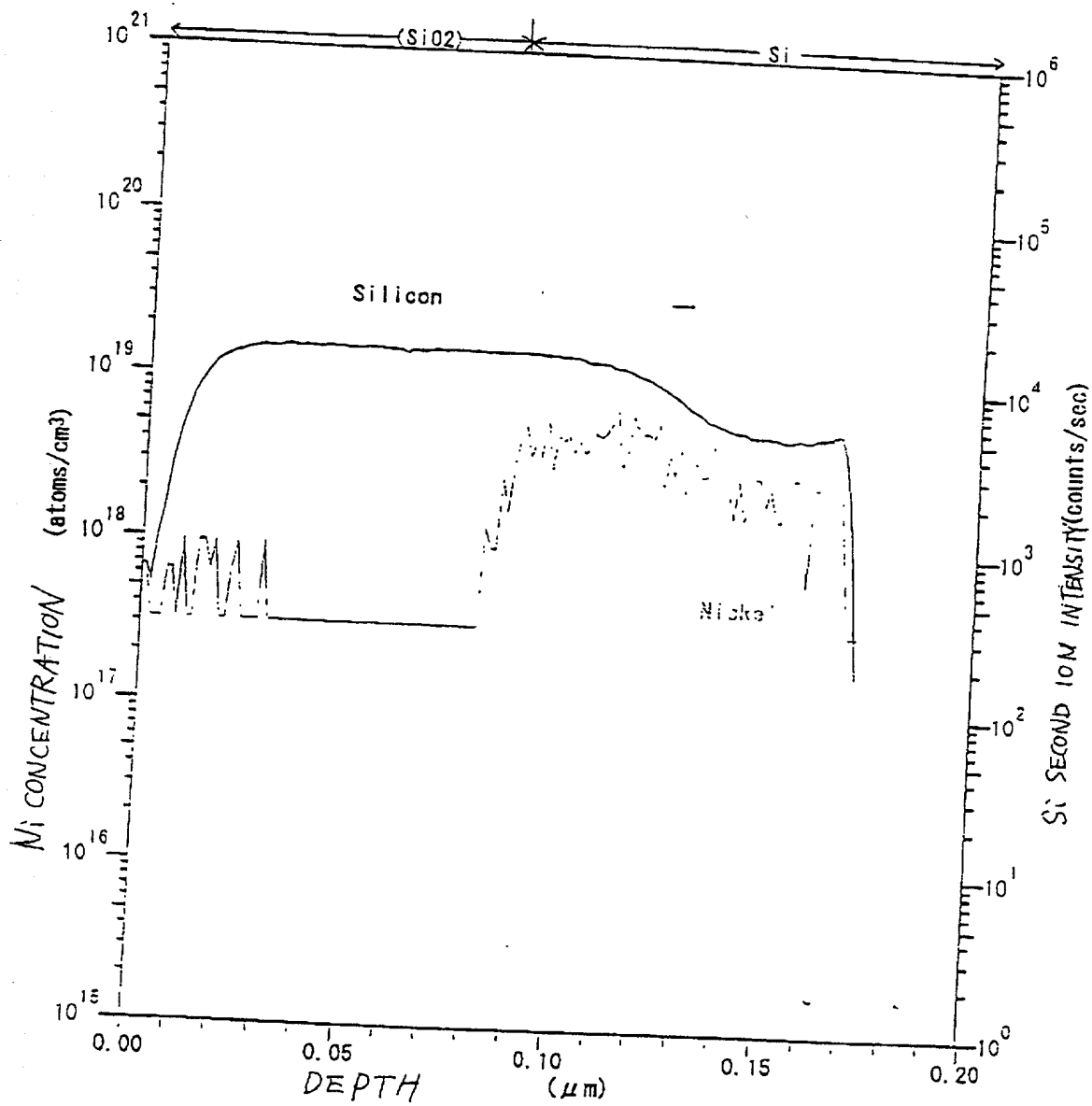


FIG. 20

20270-6684007

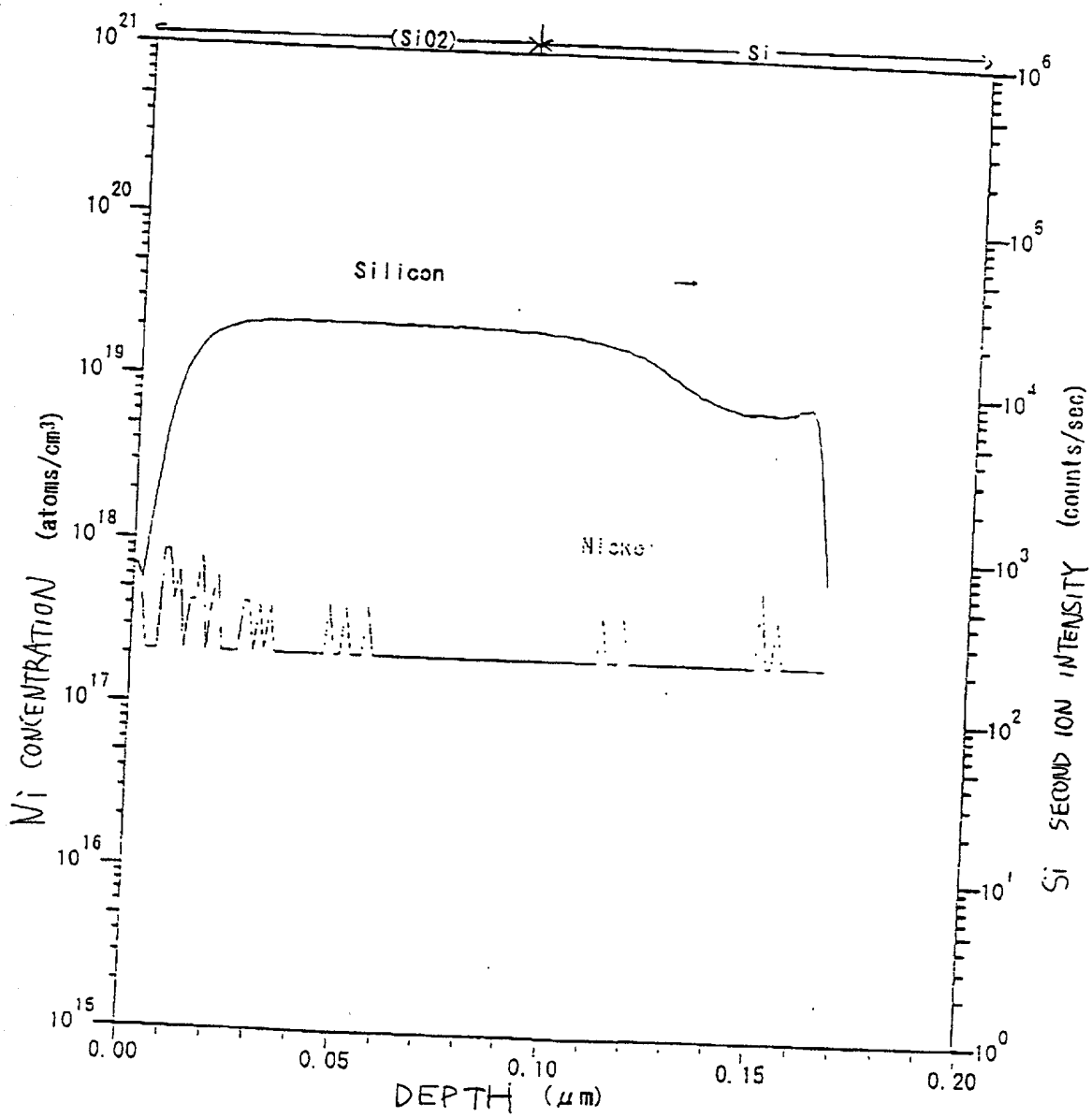


FIG. 21

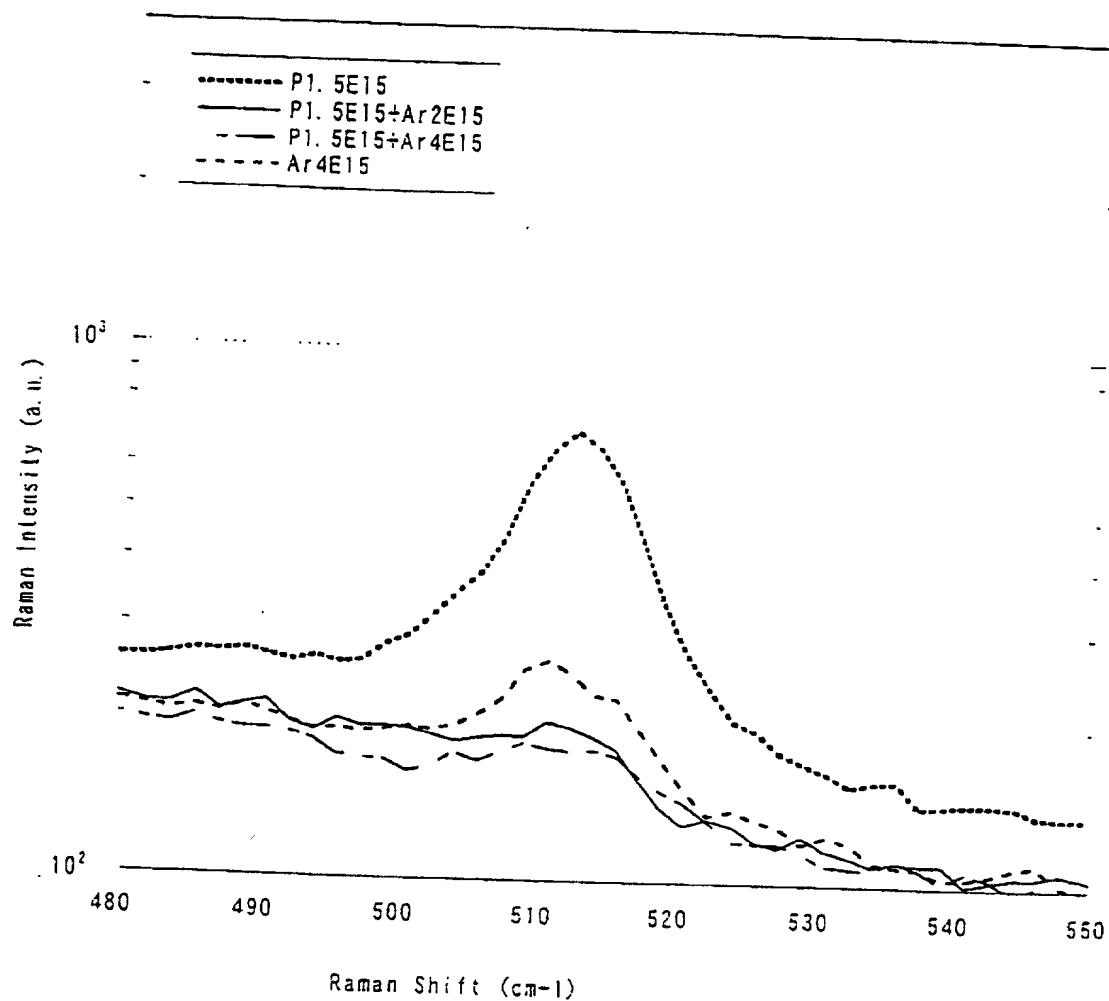


FIG. 22

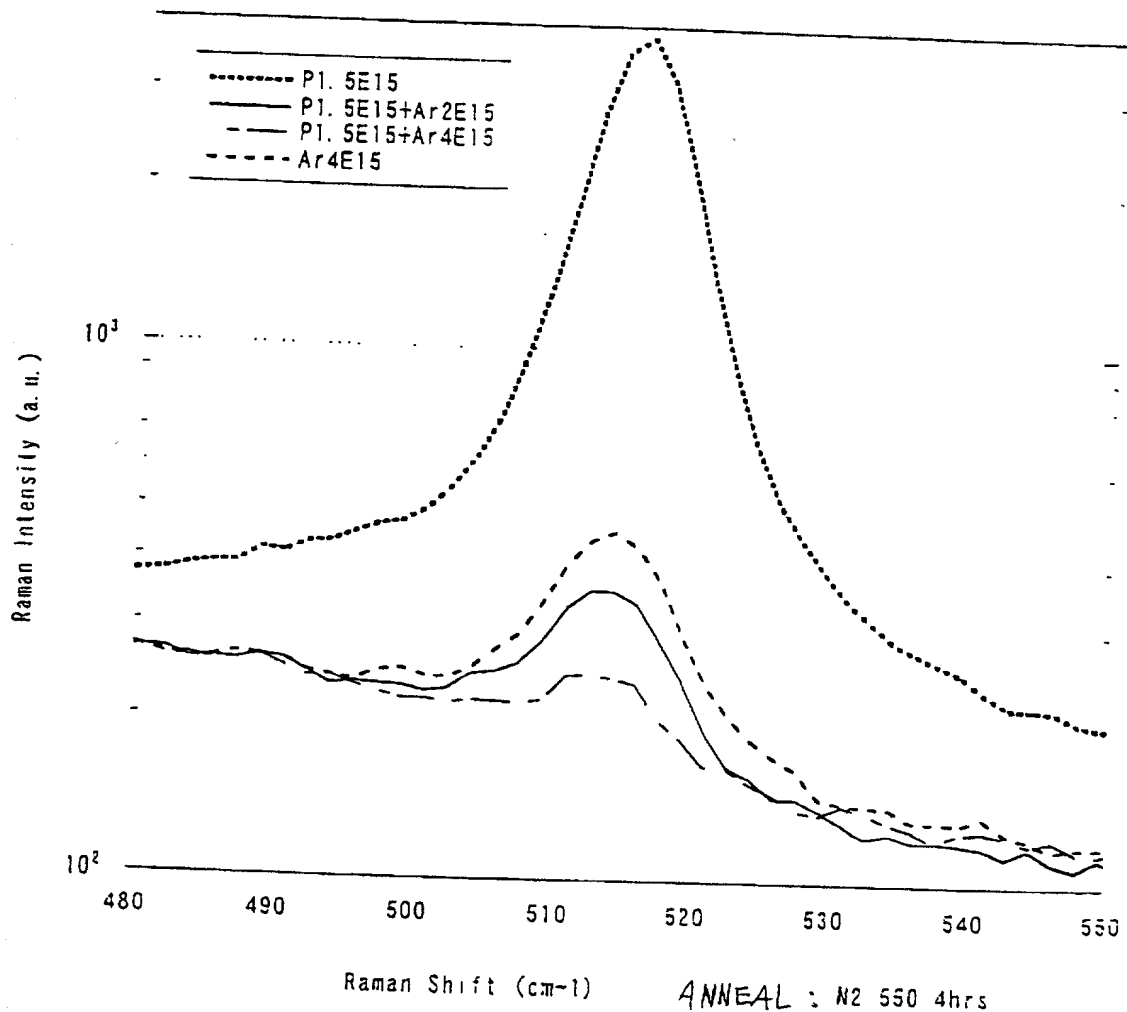


FIG. 23

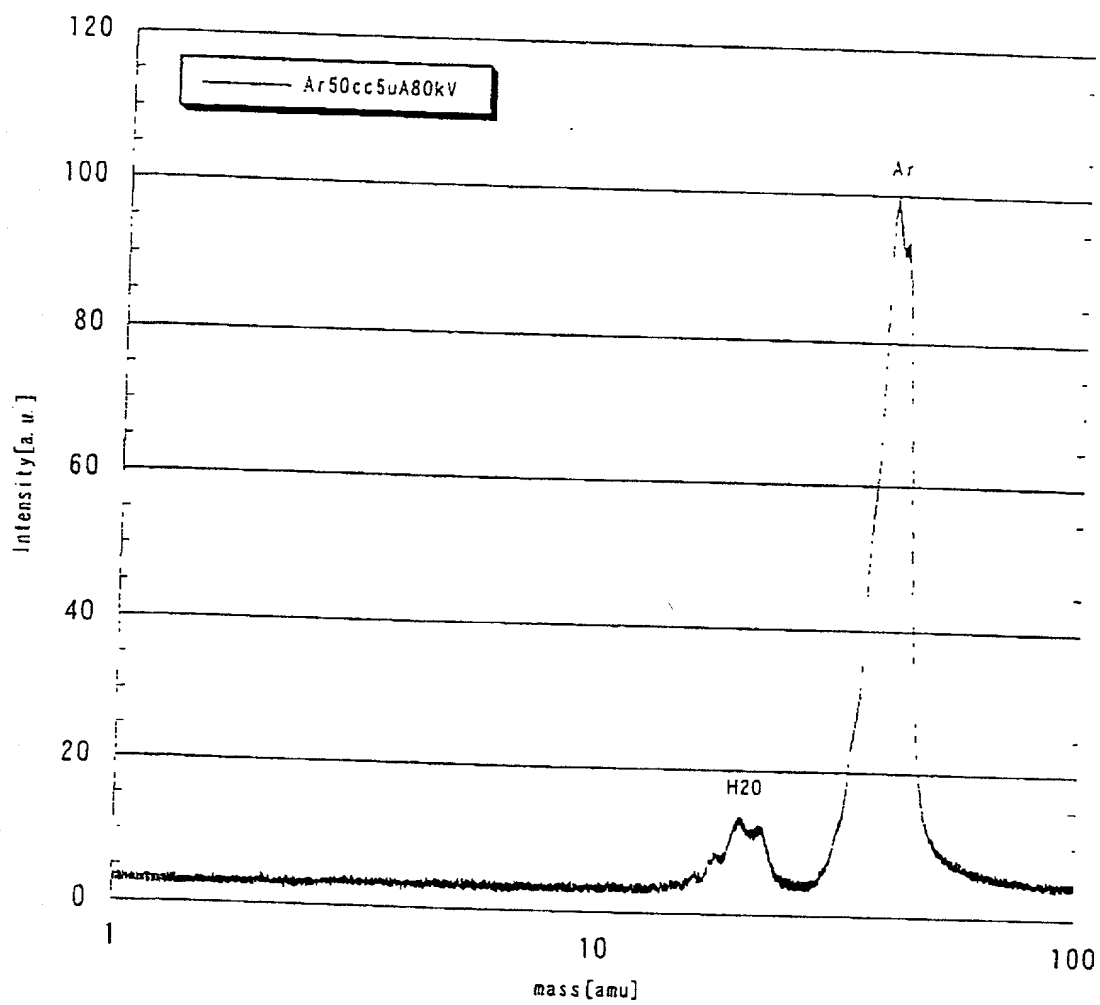
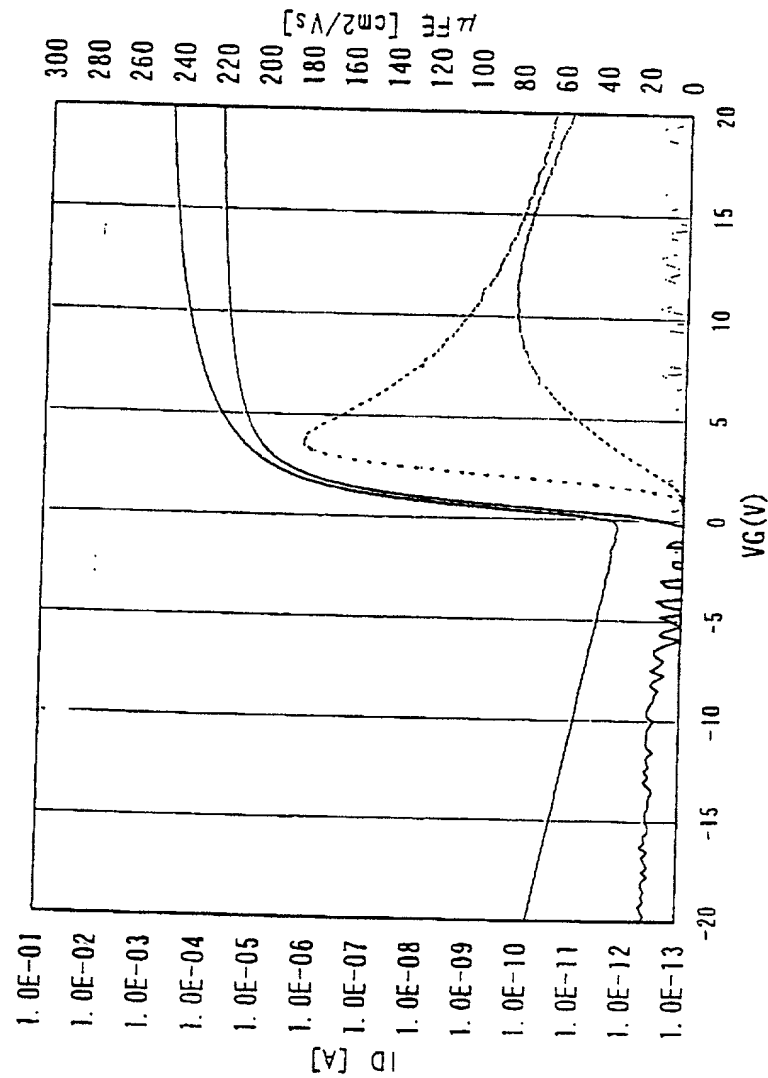


FIG. 24



A P 0 0 5 - 1 7, Units X A 3 Y 11 (C), N-ch, L/W= 7/ 8,  
 Tox= 115)



Lot No. :	AP005 CN
FILE NAME	CHNSA311
Comment	SemiAuto
PARAMETER OF MEASUREMENT	
VD start	1
VD step	13
VD step number	2
PARAMETER OF CALCULATION	
CHANNEL TYPE	N
L [um]	7.0
W [um]	8.0
DIELECTRIC CONSTANT	4.1
THICKNESS OF OXIDE	115
RESULT OF CALCULATION	
Ion_2 [2.34E-04]	
Ioff_2 [3.70E-12]	
Shift_1[V]	0.231
Vth [V]	1.222
S-value [V/dec]	0.175
μFE (max) [cm2/Vs]	179.9

FIG. 25

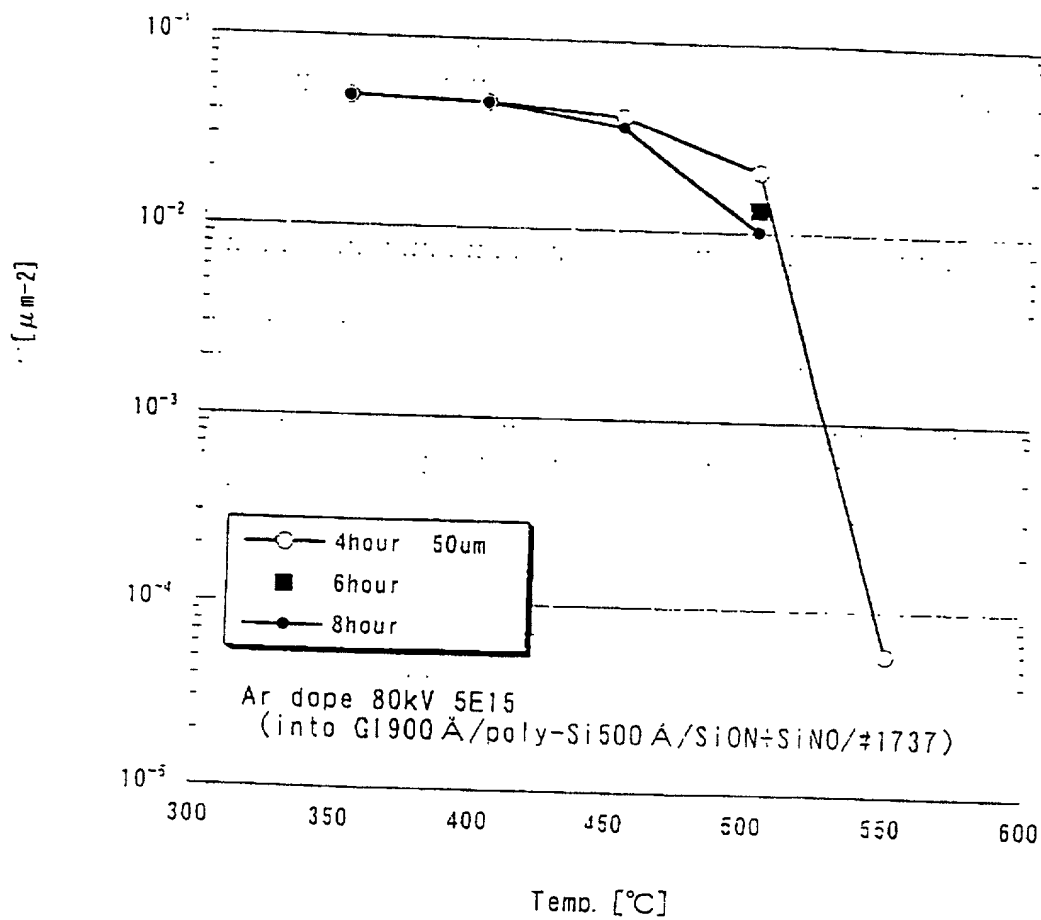


FIG. 26

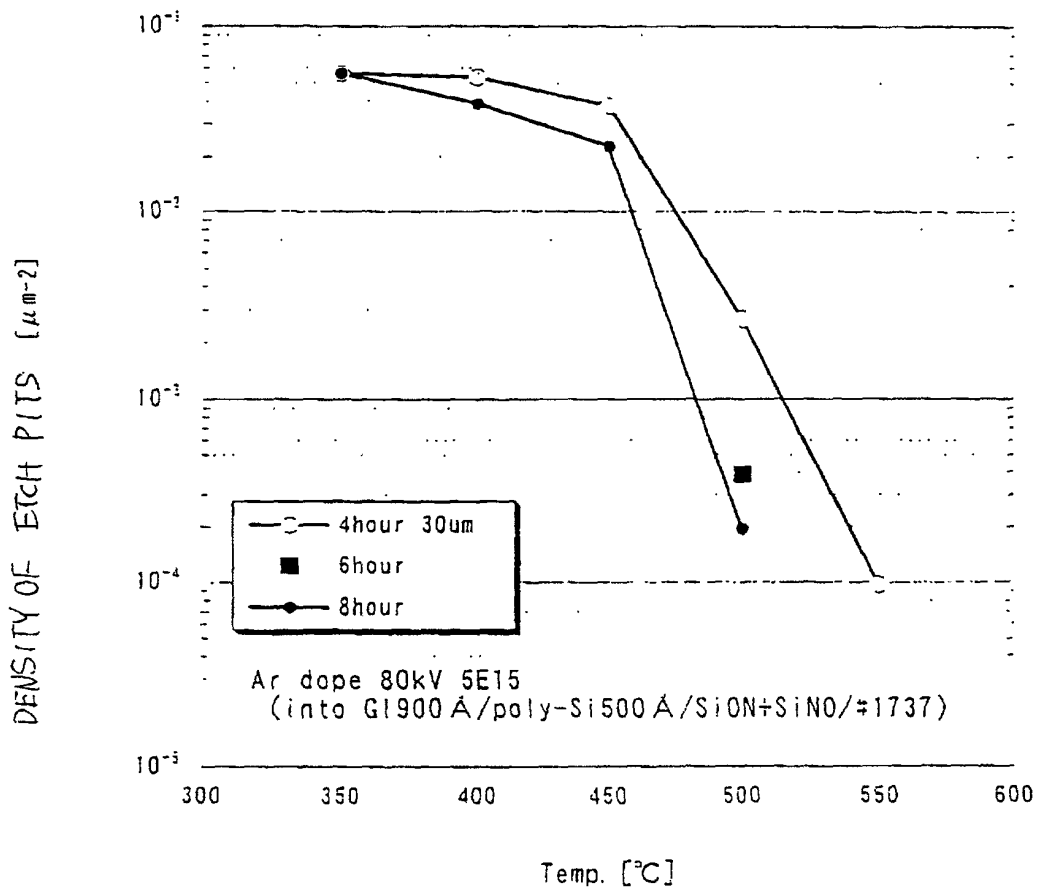


FIG. 27

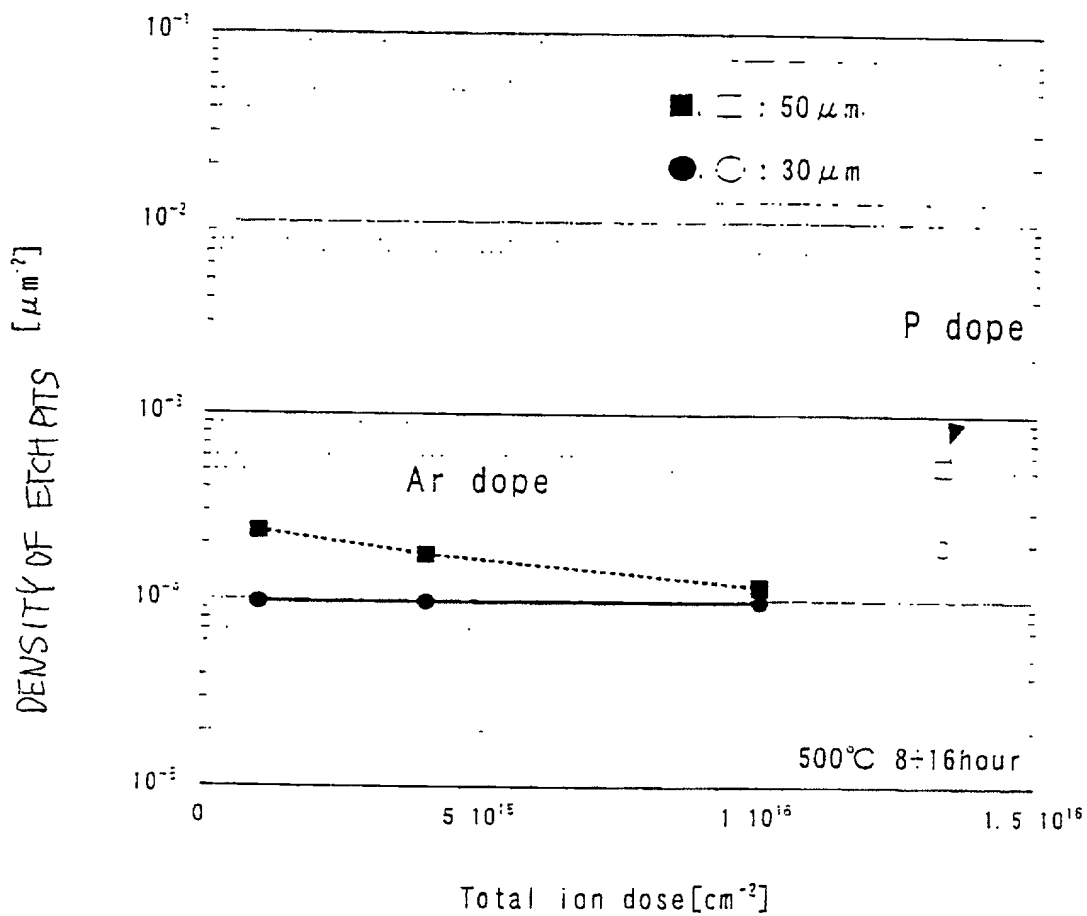


FIG. 28

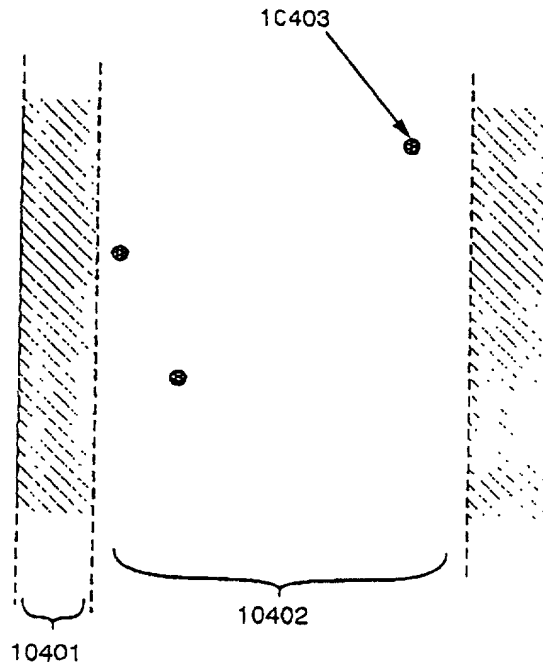
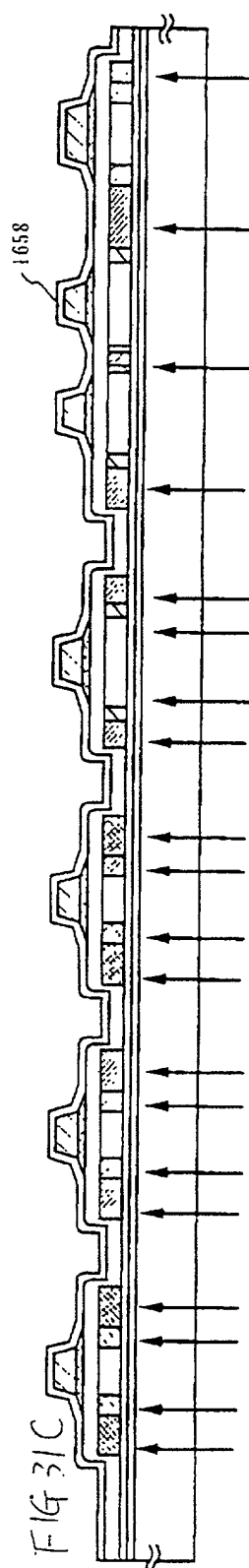
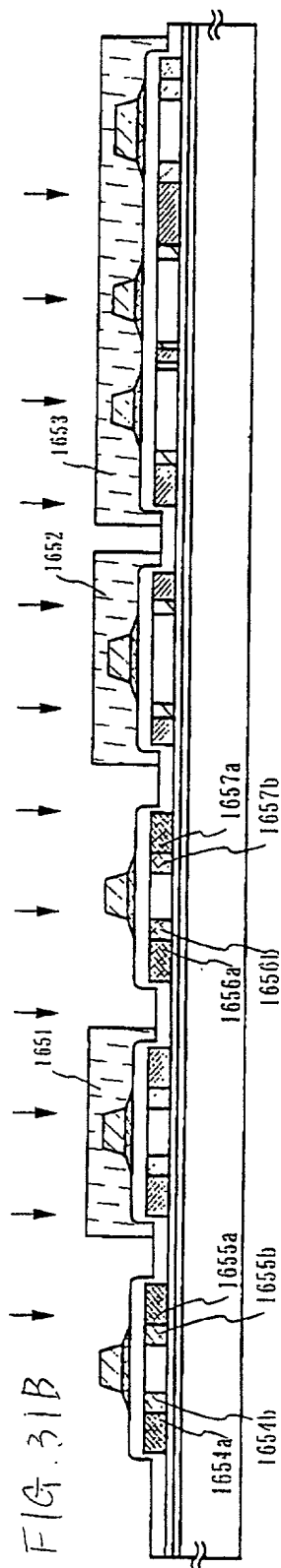
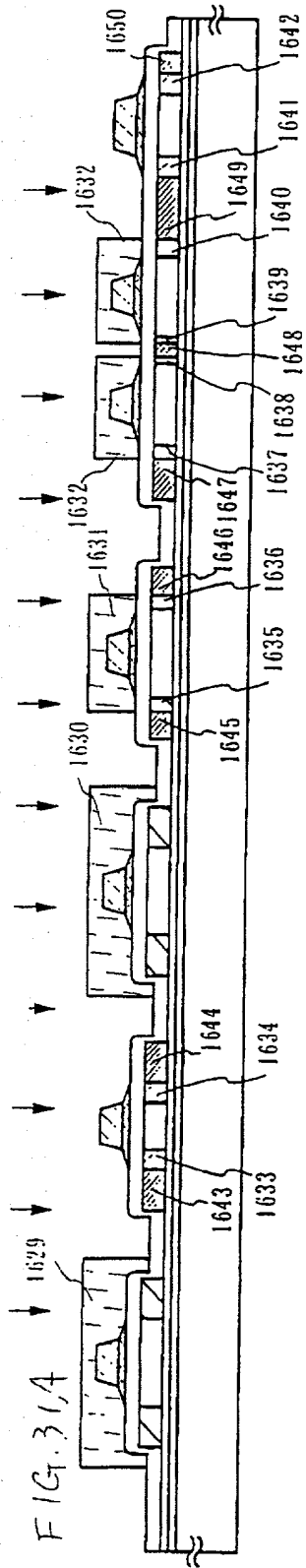


FIG. 29

A cross-sectional view of a multi-layered structure 1600. The structure consists of a series of alternating layers and cavities. From left to right, the layers are labeled 1602, 1603, 1604, 1605, 1606, and 1607. The cavities between these layers are labeled 1601, 1608, and 1609. The layers 1602, 1603, 1604, and 1605 are shown with a hatched pattern, while layers 1606 and 1607 are shown with a solid pattern. The cavities 1601, 1608, and 1609 are shown with a solid pattern. The entire structure is labeled 1600.

FIG. 30B is a cross-sectional view of a semiconductor device. It shows a series of rectangular blocks (1610, 1611, 1612, 1613, 1614, 1615) arranged along a common bus line (1620). Each block is connected to the bus line via a contact (1621a, 1621b). The blocks are separated by insulating regions (1616a, 1616b, 1617a, 1617b, 1618a, 1618b, 1619a, 1619b). The bus line is connected to a power supply (VDD) and a ground (GND) terminal.



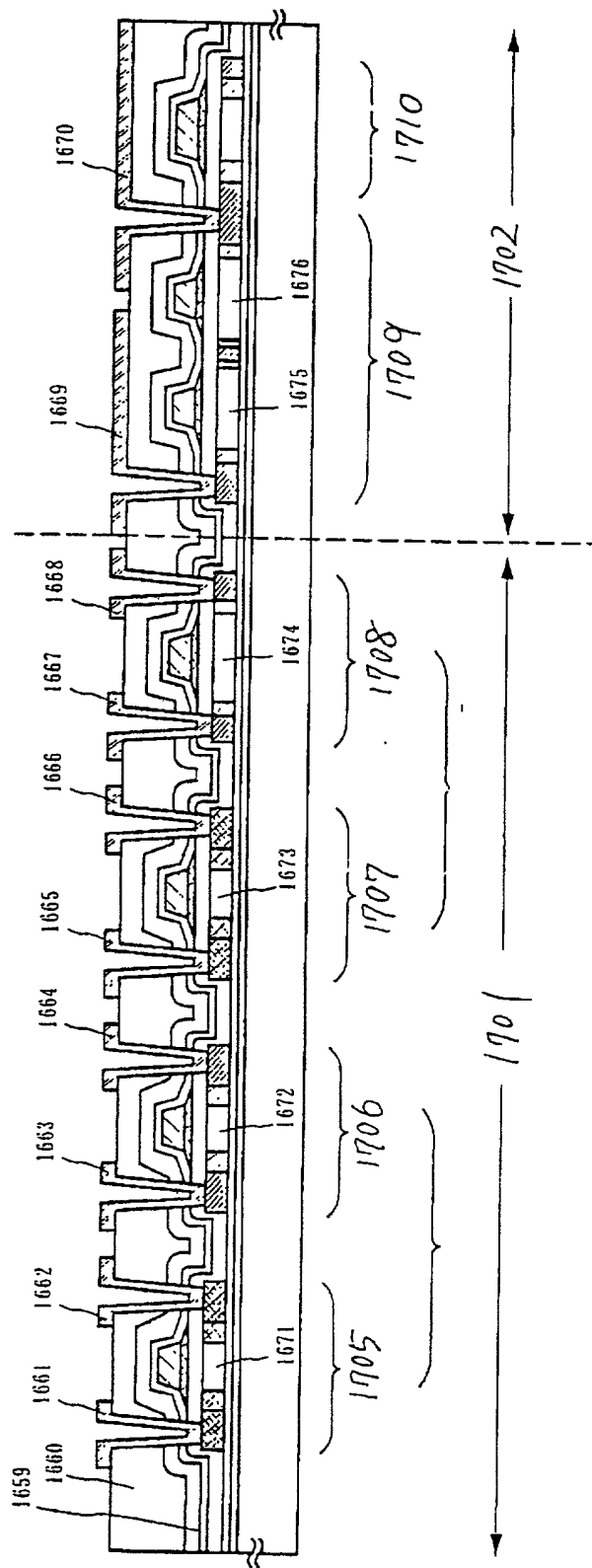


FIG. 32



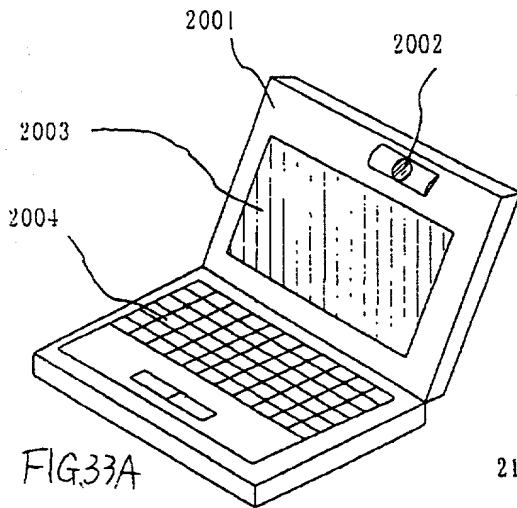


FIG. 33A

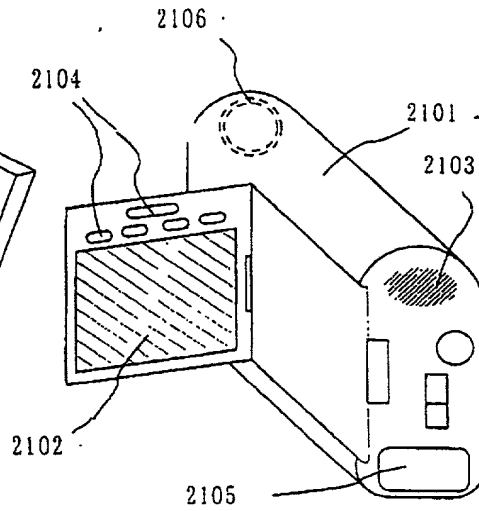


FIG. 33B

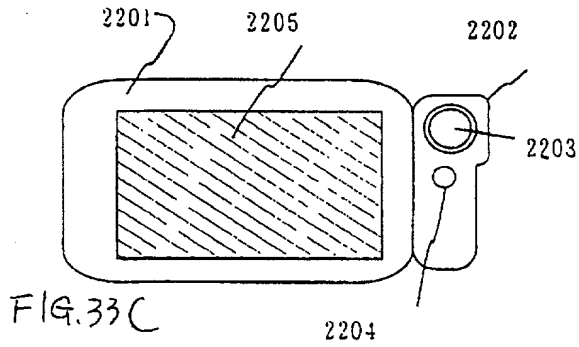


FIG. 33C

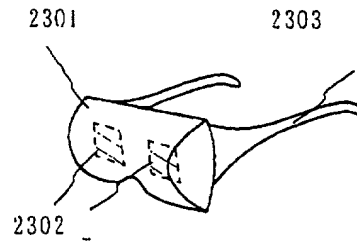


FIG. 33D

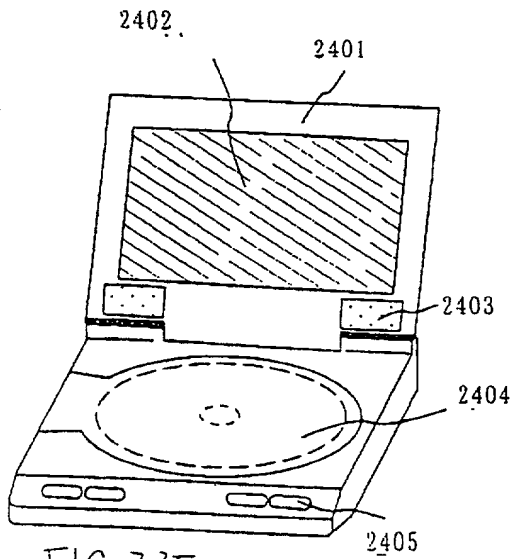


FIG. 33E

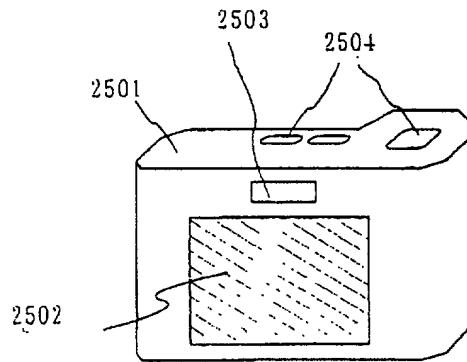


FIG. 33F

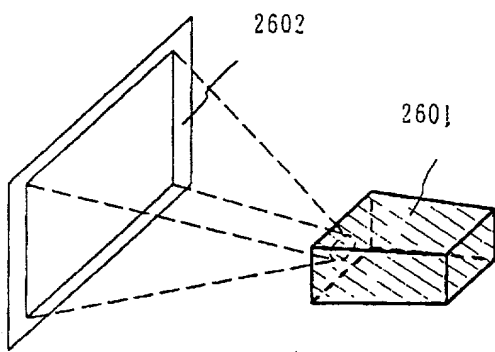


FIG. 34A

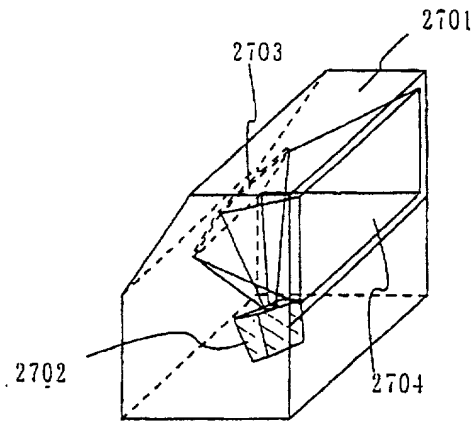


FIG. 34B

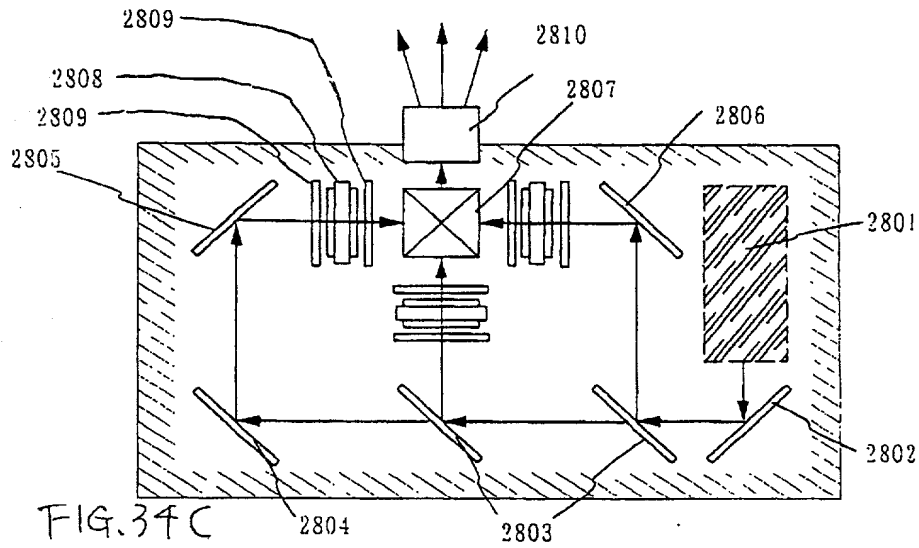


FIG. 34C

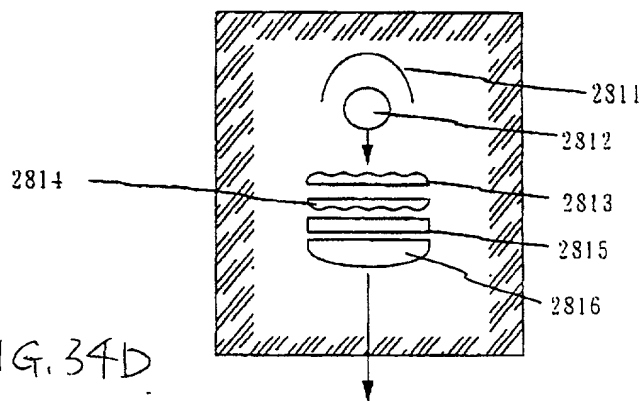


FIG. 34D

FIG. 35A

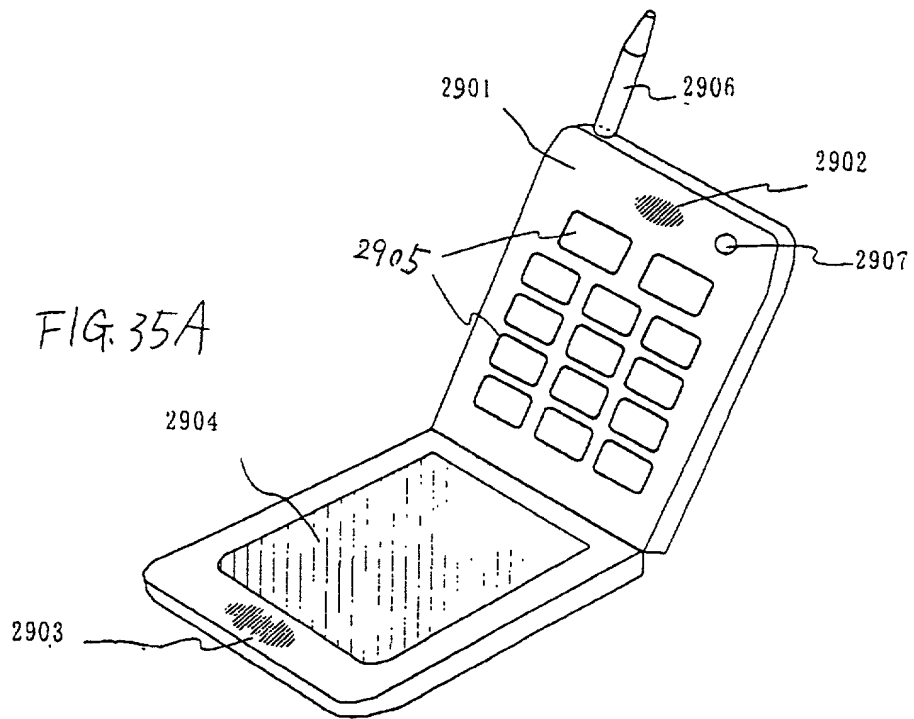


FIG. 35B

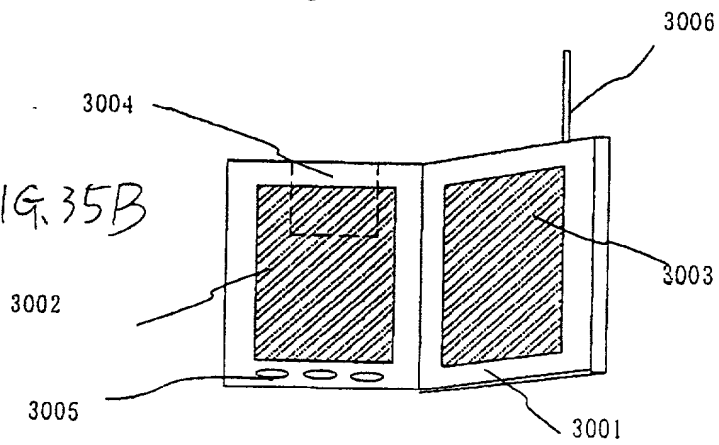
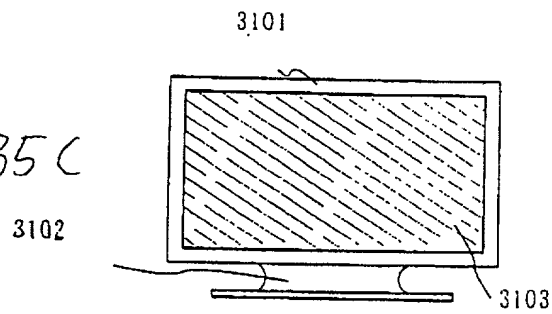


FIG. 35C




	GETTERING CONDITION
MAGNIFICATION	550°C4hrs
x 200	

FIG. 36